

Exam. Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
/PB/	1	6,262,462	7/17/2001	Marshall, et al.			
/PB/	2	5,721,145	2/24/1998	Kusakabe, et al.			
/PB/	3	2002/093046 A1	7/18/2002	Moriya, et al.			

Exam. Initials		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
/PB/	1	WO 2004/112147 A1	12/23/2004	WIPO				
/PB/	2	EP 1 164 636 A2	12/19/2001	EPO				
/PB/	3	JP 05082777	4/2/1993	JPO				

/PB/	1	Ota et al, <i>Novel Locally Strained Channel Technique for High Performance 55nm CMOS</i> , IEDM Technical Digest, 27-30 (2002)
/PB/	2	<i>Applying Mechanical Stress to Improve MOS Semiconductor Performance</i> , 30 IBM Technical Disclosure Bulletin, 330-333 (1988)
/PB/	3	Momose et al, <i>Relationship Between Mobility and Residual-Mechanical-Stress As Measured By Raman Spectroscopy For Nitrided-Oxide-Gate MOSFETs</i> , 90 IEDM, 65-68 (1990)
/PB/	4	Jennifer O'Connor, <i>Analytical Predictions of Thermal Stress in MOSFETs</i> , IEEE, 131-143 (1995)
/PB/	5	Wristers et al, <i>Ultra Thin Oxide Reliability: Effects of Gate Doping Concentration and Poly-Si/SiO₂ Interface Stress Relaxation</i> , IEEE, 77-83 (1996)
/PB/	6	Steegen et al, <i>Silicide-induced Stress In Si: Origin and Consequences for MOS Technologies</i> , 38 Materials Science and Engineering R: Reports, 1-53 (2002)

Page 1 of 1